

L Number	Hits	Search Text	DB	Time stamp
1	126	LIU-CHIEN-HUNG-.in. LIU-C-H-.in. PAN-SHYI-SHUH-.in. HUANG-SHOU-WEI-.in. HUANG-S-W-.in. CHEN-YING-TSO-.in. CHEN-Y-T-.in. LAI-ERH-KUN-.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:08
2	122428	read adj only adj memory	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:03
3	244879	rom!	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:03
4	221	nitride adj read adj only adj memory	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:04
5	422	nrom!	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:04
6	5216	low adj ((threshold adj voltage) vth "v.sub.th")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:04
7	3143	high adj ((threshold adj voltage) vth "v.sub.th")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:04
8	4233	ono! near2 (layer film dielectric coating material)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:10
9	704846	photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:06
12	1593	(oxide-nitride-oxide) near2 (layer film dielectric coating material)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:11
14	3	"silicon oxide/silicon nitride/silicon oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:13
16	1198	"oxide/nitride/oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:17
17	16	((nitride adj read adj only adj memory) nrom!) and (low adj ((threshold adj voltage) vth "v.sub.th")) and (high adj ((threshold adj voltage) vth "v.sub.th"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:17
18	4	((nitride adj read adj only adj memory) nrom!) and (low adj ((threshold adj voltage) vth "v.sub.th")) and (high adj ((threshold adj voltage) vth "v.sub.th")) and (photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) and (ono! near2 (layer film dielectric coating material)) ((oxide-nitride-oxide) near2 (layer film dielectric coating material)) "silicon oxide/silicon nitride/silicon oxide" "oxide/nitride/oxide")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 17:21
19	30613	field near oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:19

20	25222	(photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:20
22	20674	(photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 second!	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:20
23	83704	ion adj implant\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:20
24	29062	thermal near oxidation	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:20
25	101455	polysilicon poly-silicon (poly adj (si silicon)) poly-si polysi	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:21
26	76306	(word bit) adj line	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:21
27	820487	gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:21
28	2	("5403764").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:21
29	56	((field near oxide) and ((ono! near2 (layer film dielectric coating material)) ((oxide-nitride-oxide) near2 (layer film dielectric coating material)) "silicon oxide/silicon nitride/silicon oxide" "oxide/nitride/oxide") and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) and (ion adj implant\$6) and (thermal near oxidation) and (polysilicon poly-silicon (poly adj (si silicon)) poly-si polysi) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 second!)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:35
30	42	((field near oxide) and ((ono! near2 (layer film dielectric coating material)) ((oxide-nitride-oxide) near2 (layer film dielectric coating material)) "silicon oxide/silicon nitride/silicon oxide" "oxide/nitride/oxide") and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) and (ion adj implant\$6) and (thermal near oxidation) and (polysilicon poly-silicon (poly adj (si silicon)) poly-si polysi) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 second!)) and ((word bit) adj line) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:33

31	1	(((field near oxide) and ((ono! near2 (layer film dielectric coating material)) ((oxide-nitride-oxide) near2 (layer film dielectric coating material)) "silicon oxide/silicon nitride/silicon oxide" "oxide/nitride/oxide") and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) and (ion adj implant\$6) and (thermal near oxidation) and (polysilicon poly-silicon (poly adj (si silicon)) poly-si polysi) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 second!)) and ((word bit) adj line) and gate) and ((nitride adj read adj only adj memory) nrom!) and (low adj ((threshold adj voltage) vth "v.sub.th")) and (high adj ((threshold adj voltage) vth "v.sub.th"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:23
32	25	(((field near oxide) and ((ono! near2 (layer film dielectric coating material)) ((oxide-nitride-oxide) near2 (layer film dielectric coating material)) "silicon oxide/silicon nitride/silicon oxide" "oxide/nitride/oxide") and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) and (ion adj implant\$6) and (thermal near oxidation) and (polysilicon poly-silicon (poly adj (si silicon)) poly-si polysi) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 second!)) and ((word bit) adj line) and gate) and ((read adj only adj memory) rom! (nitride adj read adj only adj memory) nrom!)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:26
33	6	(((field near oxide) and ((ono! near2 (layer film dielectric coating material)) ((oxide-nitride-oxide) near2 (layer film dielectric coating material)) "silicon oxide/silicon nitride/silicon oxide" "oxide/nitride/oxide") and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) and (ion adj implant\$6) and (thermal near oxidation) and (polysilicon poly-silicon (poly adj (si silicon)) poly-si polysi) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 second!)) and ((word bit) adj line) and gate) and ((read adj only adj memory) rom! (nitride adj read adj only adj memory) nrom!)) and ((low adj ((threshold adj voltage) vth "v.sub.th")) (high adj ((threshold adj voltage) vth "v.sub.th"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:24

34	8	((field near oxide) and ((ono! near2 (layer film dielectric coating material)) ((oxide-nitride-oxide) near2 (layer film dielectric coating material)) "silicon oxide/silicon nitride/silicon oxide" "oxide/nitride/oxide") and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) and (ion adj implant\$6) and (thermal near oxidation) and (polysilicon poly-silicon (poly adj (si silicon)) poly-si polysi) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 second!)) and ((word bit) adj line) and gate) and ((nitride adj read adj only adj memory) nrom!))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:26
35	1	((field near oxide) and ((ono! near2 (layer film dielectric coating material)) ((oxide-nitride-oxide) near2 (layer film dielectric coating material)) "silicon oxide/silicon nitride/silicon oxide" "oxide/nitride/oxide") and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) and (ion adj implant\$6) and (thermal near oxidation) and (polysilicon poly-silicon (poly adj (si silicon)) poly-si polysi) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 second!)) and ((word bit) adj line) and gate) and (low adj ((threshold adj voltage) vth "v.sub.th")) and (high adj ((threshold adj voltage) vth "v.sub.th"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:33
36	2	((ono! near2 (layer film dielectric coating material)) ((oxide-nitride-oxide) near2 (layer film dielectric coating material)) "silicon oxide/silicon nitride/silicon oxide" "oxide/nitride/oxide") and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 second!) and (ion adj implant\$6) and (thermal near oxidation) and (low adj ((threshold adj voltage) vth "v.sub.th")) and (high adj ((threshold adj voltage) vth "v.sub.th"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:36
37	2	((ono! near2 (layer film dielectric coating material)) ((oxide-nitride-oxide) near2 (layer film dielectric coating material)) "silicon oxide/silicon nitride/silicon oxide" "oxide/nitride/oxide") and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 second!) and (low adj ((threshold adj voltage) vth "v.sub.th")) and (high adj ((threshold adj voltage) vth "v.sub.th"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:37

38	271	((ono! near2 (layer film dielectric coating material)) ((oxide-nitride-oxide) near2 (layer film dielectric coating material)) "silicon oxide/silicon nitride/silicon oxide" "oxide/nitride/oxide") and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 second!))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:37
39	8	((ono! near2 (layer film dielectric coating material)) ((oxide-nitride-oxide) near2 (layer film dielectric coating material)) "silicon oxide/silicon nitride/silicon oxide" "oxide/nitride/oxide") and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 second!)) and (nitride adj read adj only adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:38
40	1743	(low adj ((threshold adj voltage) vth "v.sub.th")) and (high adj ((threshold adj voltage) vth "v.sub.th"))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:38
41	6	((low adj ((threshold adj voltage) vth "v.sub.th")) and (high adj ((threshold adj voltage) vth "v.sub.th"))) and 430/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:38
42	29	((low adj ((threshold adj voltage) vth "v.sub.th")) and (high adj ((threshold adj voltage) vth "v.sub.th"))) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 second!))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:38
43	33	((low adj ((threshold adj voltage) vth "v.sub.th")) and (high adj ((threshold adj voltage) vth "v.sub.th"))) and 430/\$.ccls.) (((low adj ((threshold adj voltage) vth "v.sub.th")) and (high adj ((threshold adj voltage) vth "v.sub.th"))) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 second!))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:40
44	616	((read adj only adj memory) rom!) near3 implant\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:40
45	2483	threshold with voltage with adjust\$4 with implant\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:41
46	15	((((read adj only adj memory) rom!) near3 implant\$5) (threshold with voltage with adjust\$4 with implant\$5)) and 430/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:41

48	45	(((low adj ((threshold adj voltage) vth "v.sub.th")) and (high adj ((threshold adj voltage) vth "v.sub.th")) and 430/\$.ccls.) (((low adj ((threshold adj voltage) vth "v.sub.th")) and (high adj ((threshold adj voltage) vth "v.sub.th")) and ((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) and ((photoresist resist photo-resist photosensitive (sensitive near (photo light radiation energy))) near2 second!))) (((read adj only adj memory) rom!) near3 implant\$5) (threshold with voltage with adjust\$4 with implant\$5) and 430/\$.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 16:41
49	60	((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) same ((ono! near2 (layer film dielectric coating material)) ((oxide-nitride-oxide) near2 (layer film dielectric coating material)) "silicon oxide/silicon nitride/silicon oxide" "oxide/nitride/oxide")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 17:21
50	16	((photoresist resist photo-resist photosensitive photo-sensitive (sensitive near (photo light radiation energy))) near2 first!) same ((ono! near2 (layer film dielectric coating material)) ((oxide-nitride-oxide) near2 (layer film dielectric coating material)) "silicon oxide/silicon nitride/silicon oxide" "oxide/nitride/oxide")) same etch\$5 same implant\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 17:27